

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1-11 (Canceled).

12. (Currently Amended) A semiconductor device, comprising:

a wiring pad;

an insulating film, formed on the wiring pad, that has plural contact holes extended to the wiring pad; and

a conducting protective layer, disposed on the wiring pad via the insulating film, that is electrically connected to the wiring pad through the plural contact holes,

wherein the plural contact holes are disposed near a periphery of the wiring pad and not disposed on the wiring pad excepting the periphery of the wiring pad.

13. (Canceled).

14. (Original) The semiconductor device according to claim 12, wherein the contact holes have a diameter of 0.5 $\mu$ m or more to about 10 $\mu$ m or less.

15. (Original) A semiconductor device, comprising:  
an insulating film having an opening;  
plural insulating pillars disposed in the opening;  
a wiring pad embedded in the opening to extend to midway of the opening; and  
a conducting protective layer to the wiring pad which is disposed on the wiring pad so to fill the opening.
16. (Original) The semiconductor device according to claim 15, wherein the plural insulating pillars have a length of 0.5 $\mu$ m or more to 10 $\mu$ m or less between the adjacent pillars.
17. (Original) The semiconductor device according to claim 12, wherein a material for the wiring pad is Cu, and a material for the conducting protective layer is Al or an Al alloy.
18. (Original) The semiconductor device according to claim 15, wherein a material for the wiring pad is Cu, and a material for the conducting protective layer is a Cu alloy, Al or an Al alloy.

19. (Original) A semiconductor device, comprising:  
a wiring disposed in a predetermined pattern above a substrate;  
a protecting conductive layer disposed on a pad section of the wiring; and  
a barrier film, disposed between the wiring and the protecting conductive layer, that is formed by stacking two pairs or more of a layer made of a predetermined metal element and a layer made of a compound mainly comprising the metal element.

20. (Original) The semiconductor device according to claim 19, wherein the barrier film has each layer configuring the pair, the each layer being formed in a thickness of 5 nm or more to 30 nm or less.

21. (Original) The semiconductor device according to claim 19, wherein the barrier film is formed by stacking six pairs or less.

22. (Original) The semiconductor device according to claim 19, wherein the barrier film is formed of the same pairs only.

23. (Original) The semiconductor device according to claim 19, wherein the metal element is selected from Group IVa, Group Va or Group VIa.

24. (Original) The semiconductor device according to claim 23, wherein the compound is nitride.

25. (Original) The semiconductor device according to claim 24, wherein the wiring is formed of Cu, the protecting conductive layer is formed of Al, and the barrier film is formed of the pairs of Ta and Ta<sub>2</sub>N.

26. (New) The semiconductor device according to claim 15, wherein a material for the wiring pad is Cu, and a material for the conducting protective layer is an alloy containing copper and a metal having a higher oxidation tendency than copper.

27. (New) The semiconductor device according to claim 26, wherein the metal having the higher oxidation tendency than copper includes at least one selected from aluminum (Al), titanium (Ti), tantalum (Ta), zirconium (Zr), vanadium (V), tin (Sn), tungsten (W), cobalt (Co), iron (Fe), nickel (Ni), ruthenium (Ru), chromium (Cr), molybdenum (Mo), niobium (Nb), hafnium (Hf), magnesium (Mg), and beryllium (Be).

28. (New) The semiconductor device according to claim 26, wherein the material for the conducting protective layer is a Cu-Al alloy.

29. (New) The semiconductor device according to claim 28, wherein the Cu-Al alloy has an Al component ratio of 2 wt% to 50 wt%.